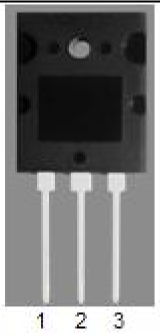
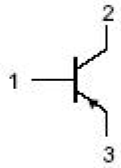
isc Silicon PNP Power Transistor 2SB1429

DESCRIPTION

- High Current Capability
- High Power Dissipation
- Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= -180V(Min)
- Complement to Type 2SD2155
- Minimum Lot-to-Lot variations for robust device performance and reliable operation





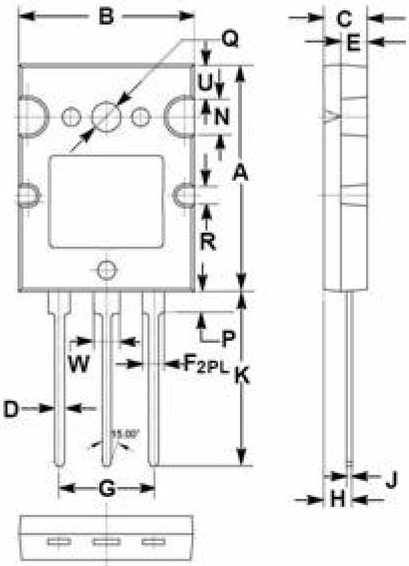
PIN: 1 Base
2 Collector
3 Emitter
TO-3PL package

APPLICATIONS

- Power amplifier applications
- Recommend for 100W high fidelity audio frequency amplifier output stage applications

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-180	V
V_{CEO}	Collector-Emitter Voltage	-180	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-15	A
I_B	Base Current-Continuous	-1.5	A
P_C	Collector Power Dissipation @ T_C=25℃	150	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



	mm	
DIM	MIN	MAX
A	25.50	26.50
B	19.80	20.20
C	4.50	5.50
D	0.90	1.10
E	2.80	3.20
F	2.40	2.60
G	10.80	11.00
H	3.10	3.30
J	0.50	0.70
K	20.00	21.00
N	3.90	4.50
P	2.40	2.60
Q	3.10	3.50
R	1.90	2.60
U	3.90	4.10
W	2.90	3.25

ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -30mA ; I_B= 0	-180			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -8A; I_B= -0.8A			-3.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C= -6A ; V_{CE}= -5V			-1.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -180V ; I_E= 0			-5	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -5V; I_C= 0			-5	μA
h_{FE-1}	DC Current Gain	I_C= -1A ; V_{CE}= -5V	55		160	
h_{FE-2}	DC Current Gain	I_C= -6A ; V_{CE}= -5V	30			
C_{OB}	Output Capacitance	I_E= 0; V_{CB}= -10V; f_{test}= 1.0MHz		340		pF
f_T	Current-Gain—Bandwidth Product	I_C= -1A ; V_{CE}= -5V		10		MHz

◆ h_{FE-1} Classifications

R	O
55-110	80-160